

## N&P-Channel complementary Power MOSFET

### Description

The HM603K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

#### N channel

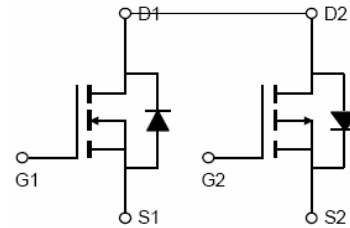
- $V_{DS} = 60V, I_D = 20A$   
 $R_{DS(ON)} < 35m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 40m\Omega @ V_{GS} = 4.5V$

#### p channel

- $V_{DS} = -60V, I_D = -12A$   
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 125m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

- H-bridge
- Inverters



Schematic diagram



Marking and pin assignment

**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM603K	HM603K	TO-252-4L			

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	$V_{DS}$	60	-60	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V	
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	20	-12	A
		$T_C = 100^\circ C$	14	-8.5	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	60	-30	A	
Maximum Power Dissipation	$P_D$	50		W	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175		$^\circ C$	

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	3	$^\circ C/W$
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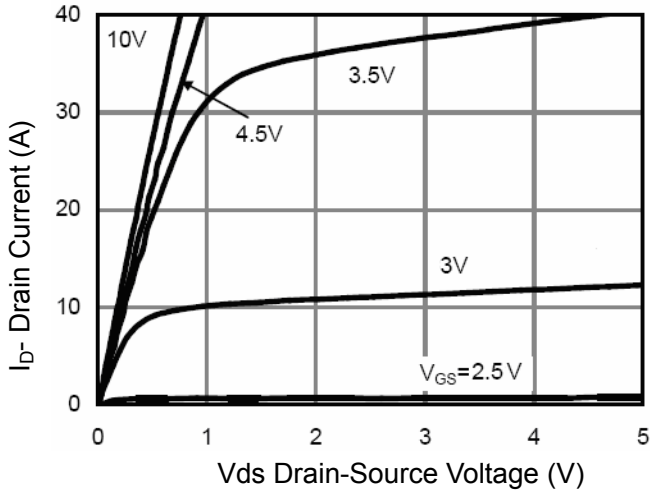
**N-Channel Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	24	35	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		30	40	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	11	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	900	-	PF
Output Capacitance	C <sub>oss</sub>		-	60	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	25	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =2A, R <sub>L</sub> =6.7Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	2.6	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	16.1	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	2.3	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =4.5A, V <sub>GS</sub> =10V	-	25	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	20	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =20A di/dt = 100A/μs (Note3)	-	29	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	49	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

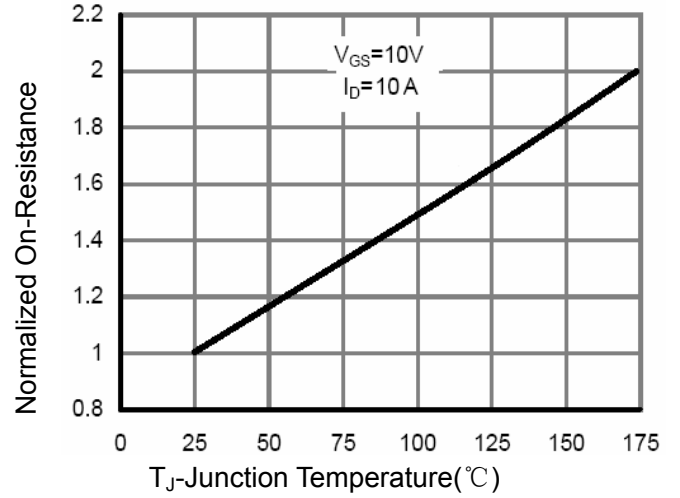
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

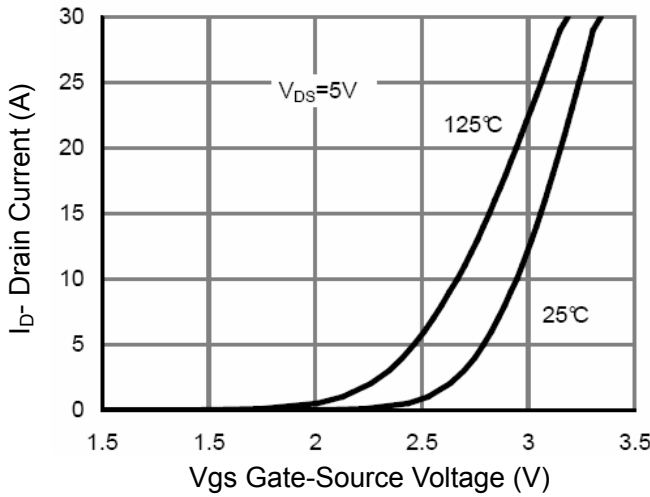
**N-Channel Typical Electrical and Thermal Characteristics (Curves)**



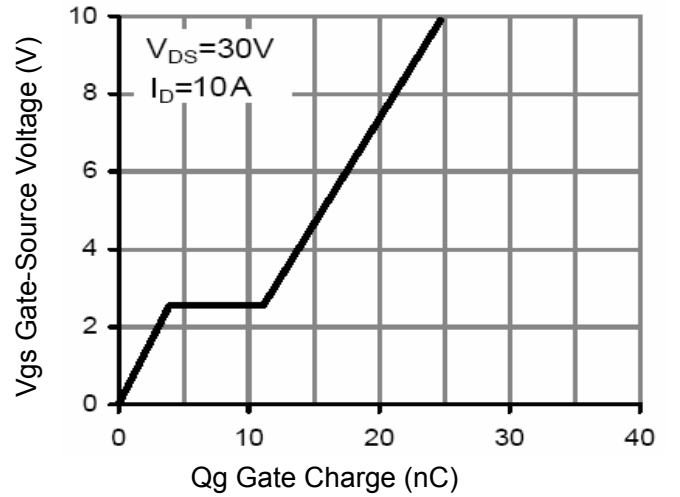
**Figure 1 Output Characteristics**



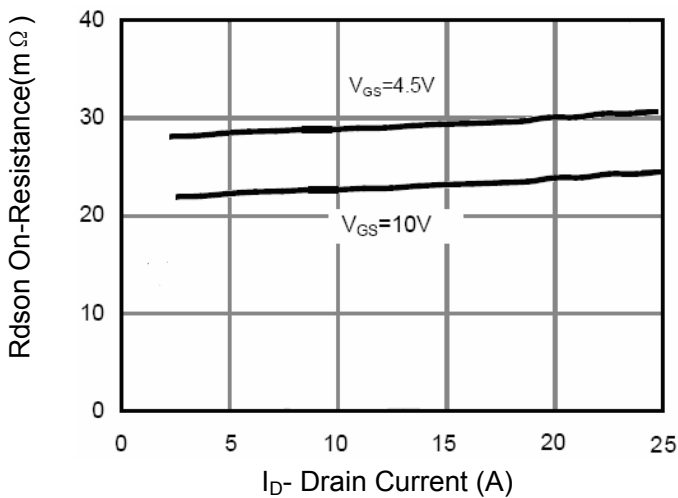
**Figure 4  $R_{dson}$ -Junction Temperature**



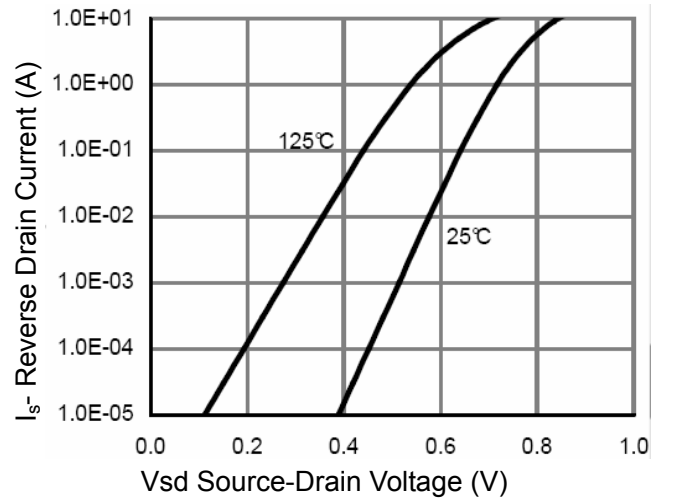
**Figure 2 Transfer Characteristics**



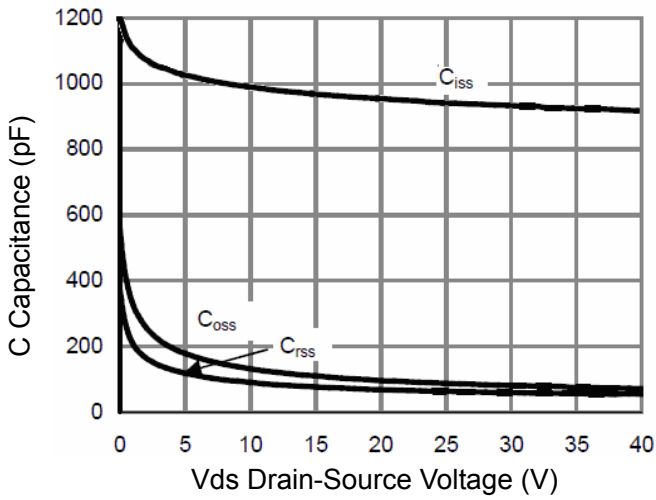
**Figure 5 Gate Charge**



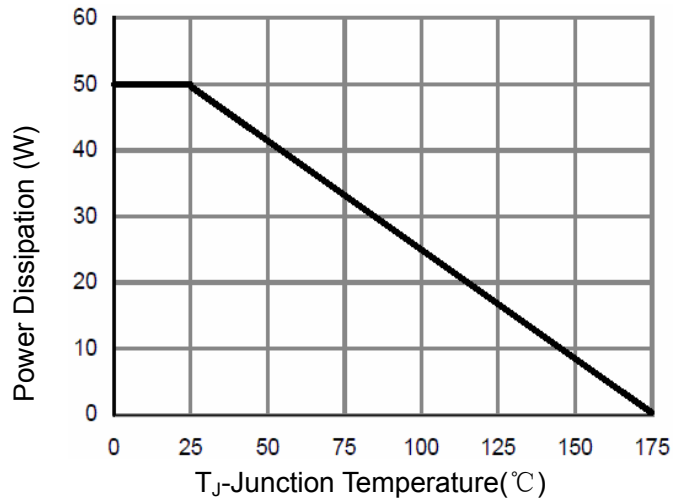
**Figure 3  $R_{dson}$ - Drain Current**



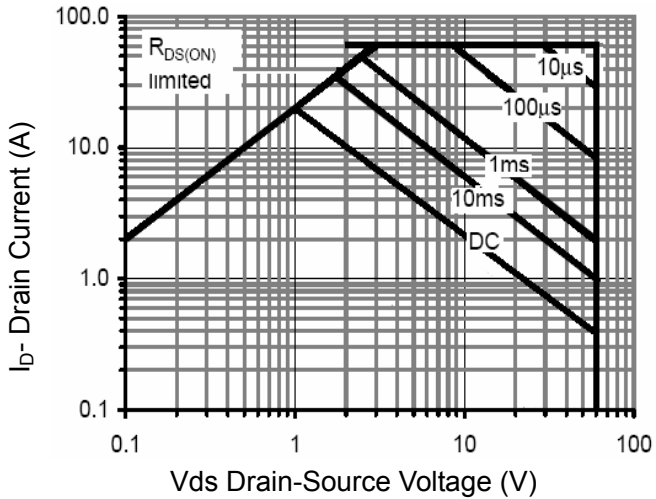
**Figure 6 Source- Drain Diode Forward**



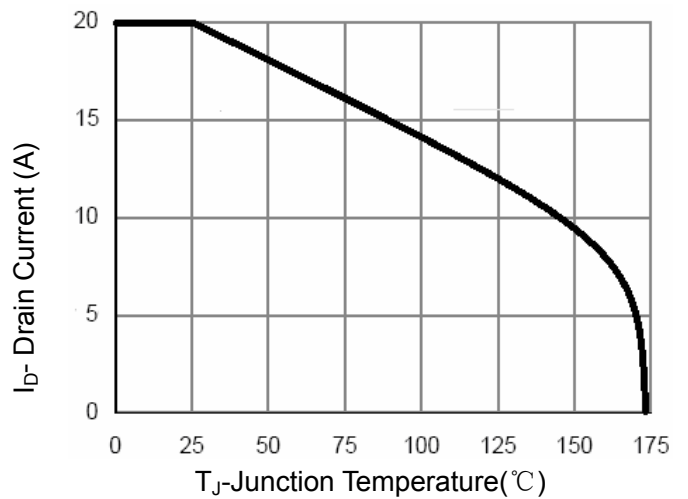
**Figure 7 Capacitance vs Vds**



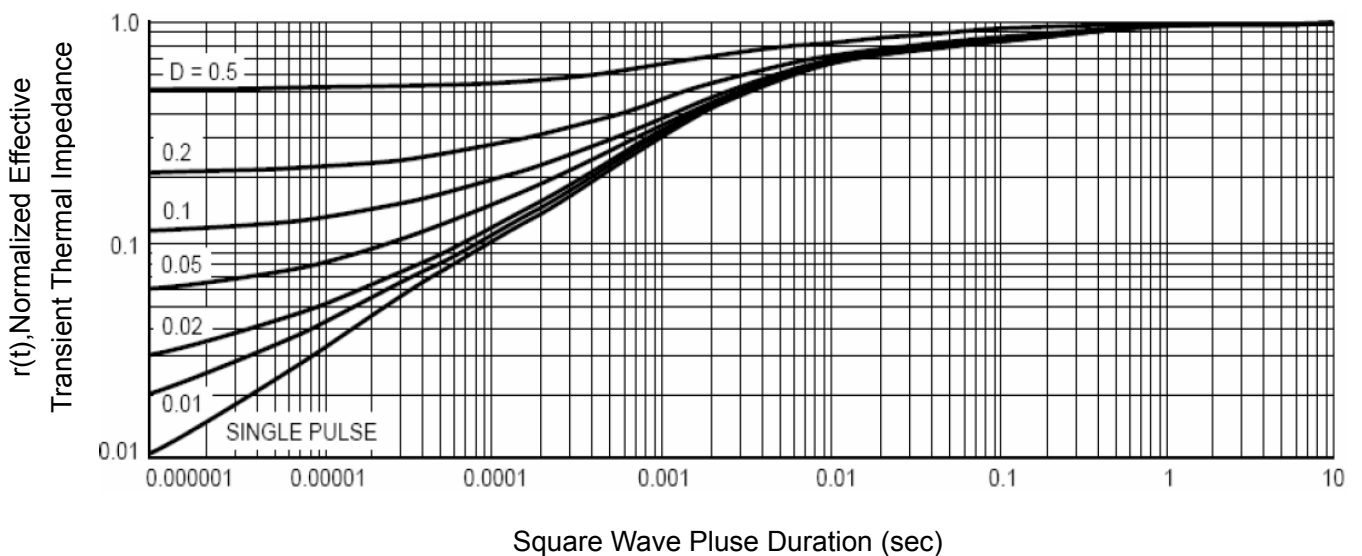
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 ID Current De-rating**

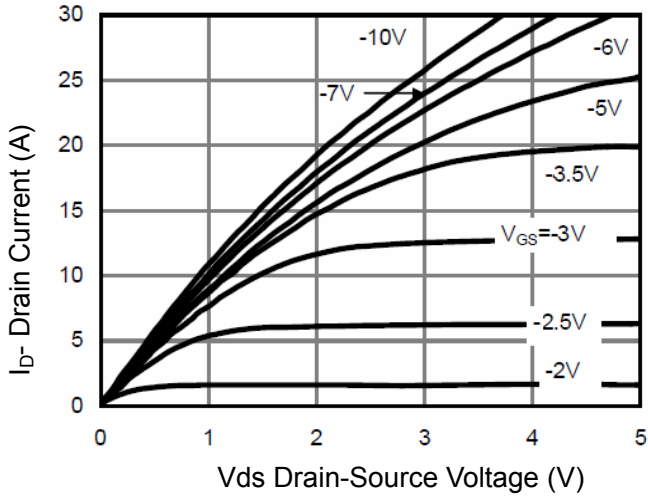


**Figure 11 Normalized Maximum Transient Thermal Impedance**

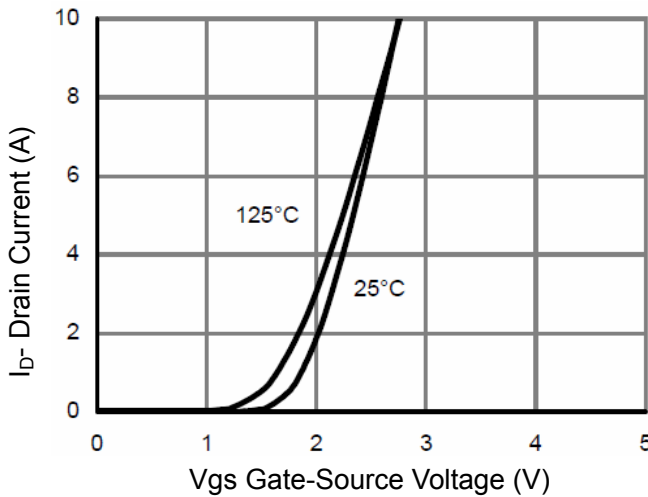
**P-Channel Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.5	-2.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-12A	-	84	100	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8A	-	100	125	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-12A	-	10	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, F=1.0MHz	-	1630.7	-	PF
Output Capacitance	C <sub>OSS</sub>		-	90.6	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	77.3	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-30V, R <sub>L</sub> =1.5Ω, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω	-	11	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	14	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	33	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	13	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-30, I <sub>D</sub> =-12A, V <sub>GS</sub> =-10V	-	37.6		nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.3		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	7.2		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-12A	-		-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-12	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = -12A	-	35		nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = -100A/μs (Note 3)	-	38		nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

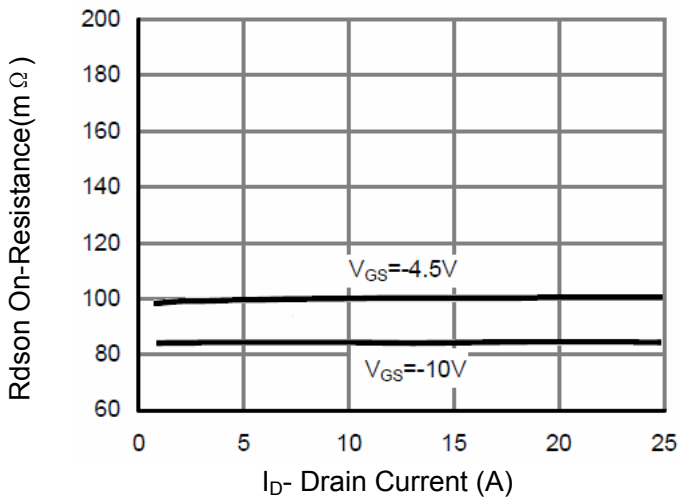
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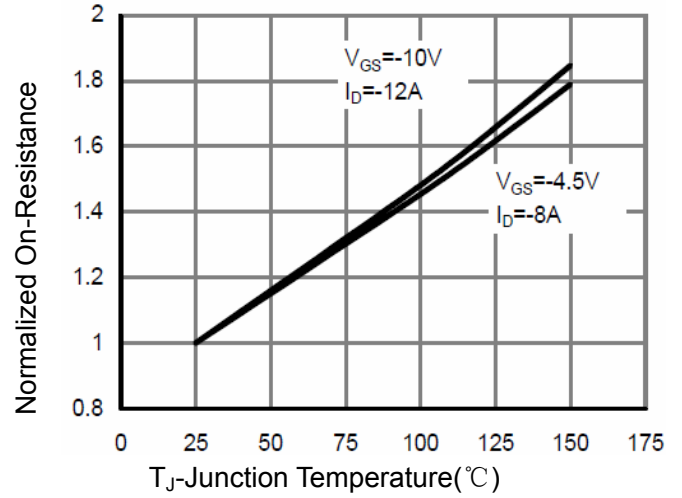
**Figure 1 Output Characteristics**



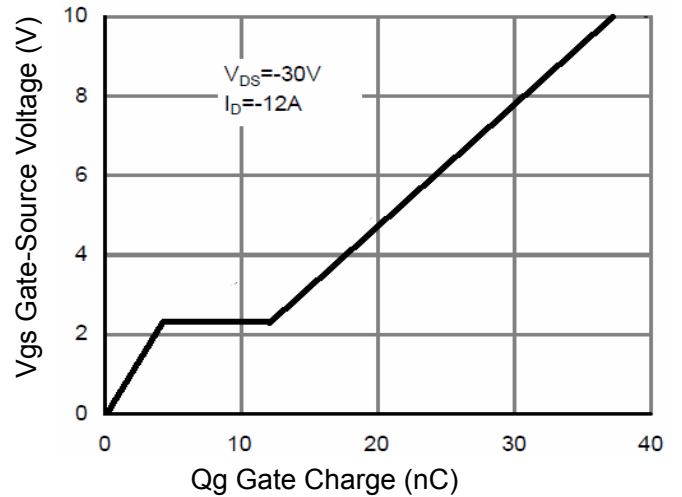
**Figure 2 Transfer Characteristics**



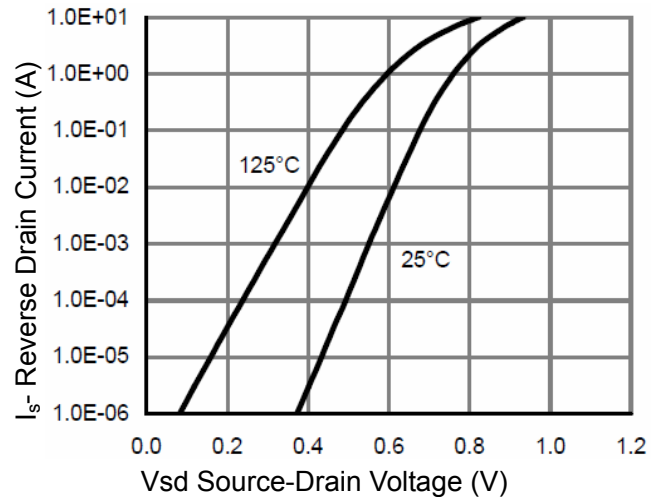
**Figure 3 Rdson- Drain Current**



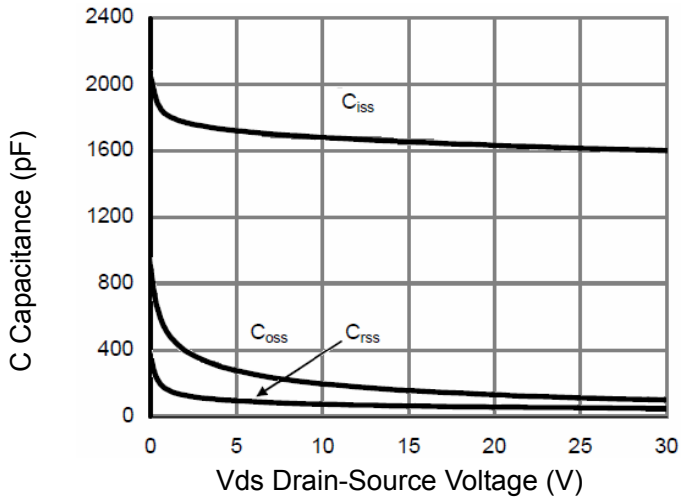
**Figure 4 Rdson-Junction Temperature**



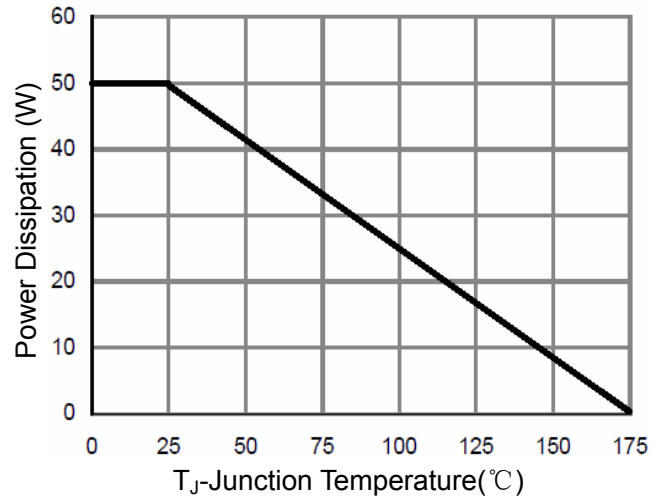
**Figure 5 Gate Charge**



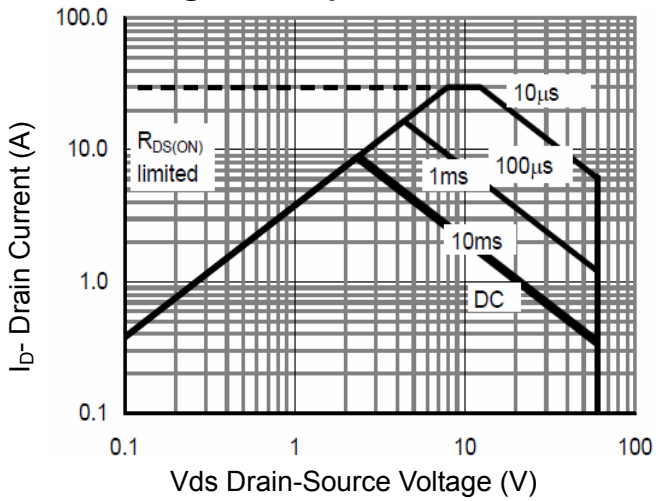
**Figure 6 Source- Drain Diode Forward**



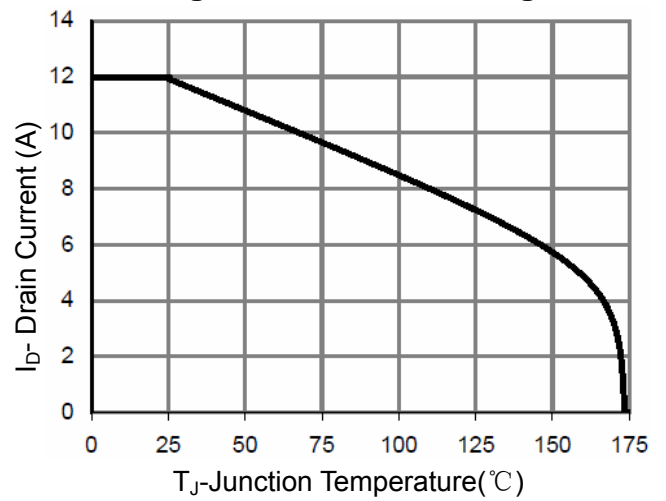
**Figure 7 Capacitance vs Vds**



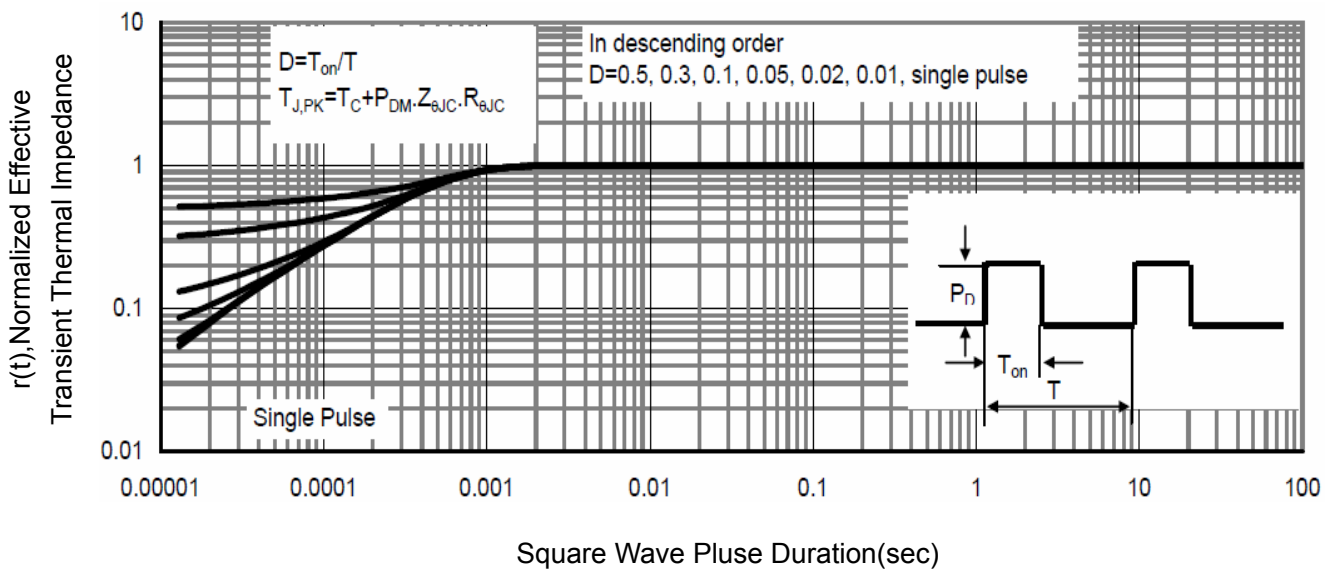
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

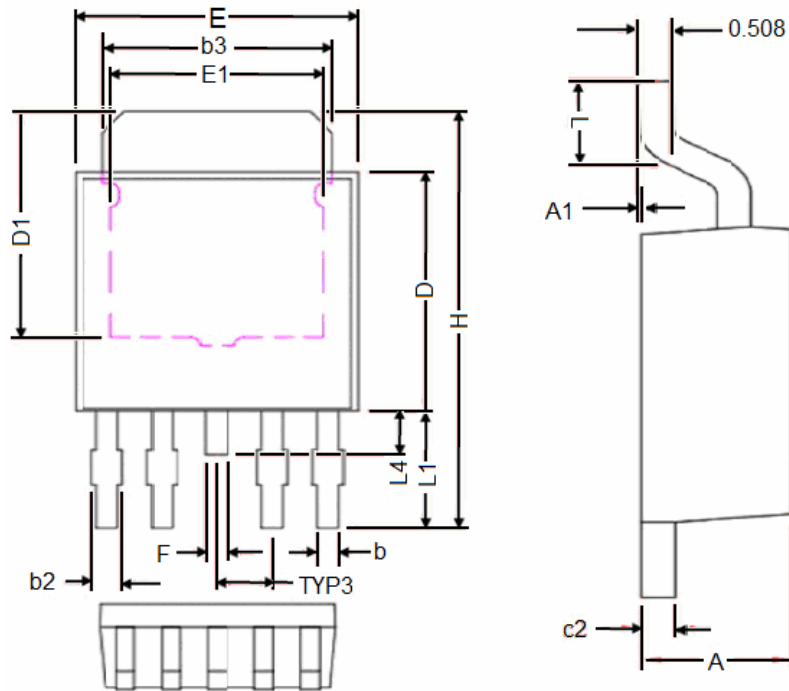


**Figure 10 ID Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

TO-252-4L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
A1	0	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	-	-
E	6.40	6.60	6.80
E1	3.81	-	-
e	1.27 REF.		
E1	3.81	-	-
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L4	0.80	1.00	1.20